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Значимые публикации	<p>1. A.Y. Polyakov, N.B. Smirnov, I.V. Shchemerov, A.V. Chernykh, E.B. Yakimov, A.I. Kochkova, A.N. Tereshchenko, S.J. Pearton. Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk SemiInsulating <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> Doped with Fe. ECS J. Solid State Sci. Technol., 8, Q3091-Q3096 (2019).</p> <p>2. A.Y. Polyakov, N.B. Smirnov, I.V. Shchemerov, E.B. Yakimov, V.I. Nikolaev, S.I. Stepanov, A.I. Pechnikov, A.V. Chernykh, K.D. Shcherbachev, A.S. Shikoh, A. Kochkova, A.A. Vasilev, S.J. Pearton. Deep trap spectra of Sn-doped Ga<sub>2</sub>O<sub>3</sub> grown by halide vapor phase epitaxy on sapphire. APL Mater. 7, 051103 (2019).</p> <p>3. A.Y. Polyakov, In-Hwan Lee, N.B. Smirnov, E.B. Yakimov, I.V. Shchemerov, A.V. Chernykh, A.I. Kochkova, A.A. Vasilev, P.H. Carey, F. Ren, D.J. Smith, S.J. Pearton. Defects at the surface of <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub> produced by Ar plasma exposure. APL Mater. 7, 061102 (2019).</p> <p>4. A. Y. Polyakov, In-Hwan Lee, N. B. Smirnov, E. B. Yakimov, I. V. Shchemerov, A. V. Chernykh, A. I. Kochkova, A. A. Vasilev, F. Ren, P. H. Carey, and S. J. Pearton. Hydrogen plasma treatment of <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub>: Changes in electrical properties and deep trap spectra. Appl. Phys. Lett. 115, 032101 (2019).</p> <p>5. A.Y. Polyakov, In-Hwan Lee, N.B. Smirnov, E.B. Yakimov, I.V. Shchemerov, A.V. Chernykh, A.I. Kochkova, A.A. Vasilev, A.S. Shiko, P.H. Carey IV, F. Ren, S.J. Pearton. Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> ECS J. Solid State Sci. Technol., 8, P661-P666 (2019).</p> <p>6. A.Y. Polyakov, V.I. Nikolaev, S.I. Stepanov, A.I. Pechnikov, E.B. Yakimov, N.B. Smirnov, I.V. Shchemerov, A.A. Vasilev, A.I. Kochkova, A.V. Chernykh, S.J. Pearton. Electrical Properties and Deep Traps in <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub>:Sn Films Grown on Sapphire by Halide Vapor Phase Epitaxy. ECS J. Solid State Sci. Technol., 2020, 9, 045003</p> <p>7. O.V. Feklisova, E.E. Yakimov, E.B. Yakimov. Study of single-layer stacking faults in 4H-SiC by deep level transient spectroscopy. Appl. Phys. Lett. 116, 172101, 2020.</p> <p>8. A.Y. Polyakov, N.B. Smirnov, I.V. Shchemerov, A.A. Vasilev, E.B. Yakimov, A.V. Chernykh, A.I. Kochkova, P.B. Lagov, Yu.S. Pavlov, O.F. Kukharchuk, A.A. Suvorov, N.S. Garanin, In-Hwan Lee, M. Xian, F. Ren, and S.J. Pearton. Pulsed fast reactor neutron irradiation effects in Si doped n-type <math>\alpha</math>-Ga<sub>2</sub>O<sub>3</sub>. J. Phys. D: Appl. Phys. 53 (2020) 274001.</p> <p>9. E.E. Yakimov, E.B. Yakimov. Radiation enhanced dislocation glide in 4H-SiC at low temperatures. J. Alloys Compds 837 (2020) 155470.</p> <p>10. E.B. Yakimov, A.Y. Polyakov, N.B. Smirnov, I.V. Shchemerov, P.S. Vergeles, E.E. Yakimov, A.V. Chernykh, M. Xian, F. Ren, S.J. Pearton. Role of hole trapping by deep acceptors in electron-beam-induced current measurements in <math>\beta</math>-Ga<sub>2</sub>O<sub>3</sub> vertical rectifiers. J. Phys. D: Appl. Phys. 53 (2020) 495108.</p>
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